

# Call for Papers

## 9th International Symposium on Control of Semiconductor Interfaces

September 5(Mon)-8(Thu), 2022  
Nagoya University, Nagoya, Japan  
<http://iscsi9.org/>

The 9th International Symposium on Control of Semiconductor Interfaces (ISCSI-IX) will be held at Nagoya University in Nagoya, Japan, on September 5-8, 2022. ISCSI is a series of highly successful meetings starting at Karuizawa, Japan, in 1993. The aim of this symposium is primarily to bring together leading-edge researchers and other interested parties in the field of science and engineering of semiconductor interfaces and related matters.

**Notice:** The world is facing the outbreak of coronavirus. The symposium platform (in-person, online, hybrid (in-person & online)) will be noted on the website: <http://iscsi9.org/> in due course. We really appreciate your understanding.

### Topic Areas

#### Thin Film Growth and Characterization

- Si, Strained Si, Ge, SiGe(C), SiC, Diamond, Silicide, Compound semiconductors
- III-nitrides, Oxide semiconductors, High-k insulator, Low-k insulator
- CVD, MBE, Selective epitaxy, Atomic layer control, Novel growth technique
- Band engineering, Defect engineering, Theory and simulation, and modeling

#### Surface and Interface Control

- Surface passivation and modification, Surface and interface chemistry, Schottky and ohmic contacts
- Atomic scale characterization of surfaces and interfaces
- Surface/interface issues in advanced devices

#### Formation and Characterization of Nanostructures

- Nanodots, Nanowires, Superlattice, 2D materials, Self-assembling, Self-organization
- Nanoscale characterization, In-situ characterization

#### Process and Device Technology

- Impurity diffusion, Dry etching, Microfabrication, Isolation
- SiGe gate, Source/drain and channel engineering, Base/emitter engineering
- SOI, SGOI, III-V on Si, Wafer bonding, Virtual substrates and their Manufacturing
- CMOS, HBT, BiCMOS, FeRAM, MODFET, SET, RTD, LED, LD, OEIC

### Submission of Papers

Paper acceptance is based on the submitted abstract. The work must be original and unpublished. Prospective authors should submit abstract(s) (only in PDF file), two pages in length including all figures and tables, by **April 24 (Sun.), 2022**, to a submission website ([https://tsys.jp/iscsi/cgi/submit\\_top.cgi](https://tsys.jp/iscsi/cgi/submit_top.cgi)). The two-page abstract must be written in English and typed in an area of 8.5×11 inches or A4 size. The first page must be headed by the title of the paper, author(s), affiliation(s), address, telephone number, and e-mail address of the corresponding author. The text of the abstract must be written to clearly and concisely explain the specific results of the work and its originality. An abstract template (Microsoft Word) is available at <http://iscsi9.org/abstract-submission>, and please follow the instructions for preparation of your abstract(s). Proceedings will be published in a special issue of Elsevier Journal, [Materials Science in Semiconductor Processing](#).

### Important dates

- Abstract Submission Deadline: April 24 (Sun.), 2022
- Notification of Acceptance: May 24 (Wed.), 2022

### **Plenary Speakers**

- Nobuyoshi Koshida, Tokyo University of Agriculture and Technology, Japan
- Satoshi Kondo, Japan Society of Newer Metals, Japan

### **Keynote Speakers**

- Hiroyuki Matsunami, Kyoto University, Japan
- Naoto Horiguchi, Interuniversity Microelectronics Centre, Belgium

### **Invited Speakers**

- Aaron Voon-Yew Thean, National University of Singapore, Singapore
- Giovanni Capellini, Innovations for High Performance Microelectronics - Leibniz Institute for High Performance Microelectronics, Germany, and Roma Tre University, Italy
- Daniel Abou-Ras, Helmholtz-Zentrum Berlin, Germany
- Inga Anita Fischer, Brandenburg University of Technology Cottbus-Senftenberg, Germany
- Norio Terada, Kagoshima University, Japan
- Reika Ichihara, Kioxia Corporation, Japan
- Takashi Tokumasu, Tohoku University, Japan
- Takayuki Harada, National Institute for Materials Science, Japan
- Takuma Kobayashi, Osaka University, Japan
- Zlatko Sitar, North Carolina State University, USA

### **Organizing Committee**

Tetsuya Yamamoto, Kochi University of Technology, Japan, Chair  
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Shun-ichiro Ohmi, Tokyo Institute of Technology, Japan

### **Symposium website**

<http://icsi9.org/>

### **Contact Info**

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